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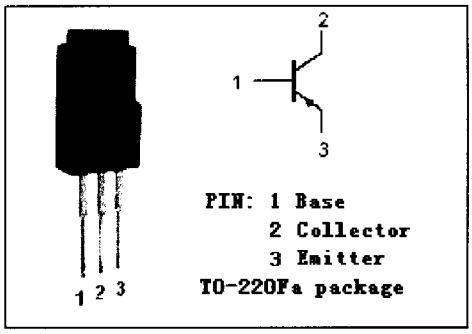
Silicon PNP Power Transistor

2SB940

DESCRIPTION

- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -150V(Min.)
- High Collector Power Dissipation
- Complement to Type 2SD1264

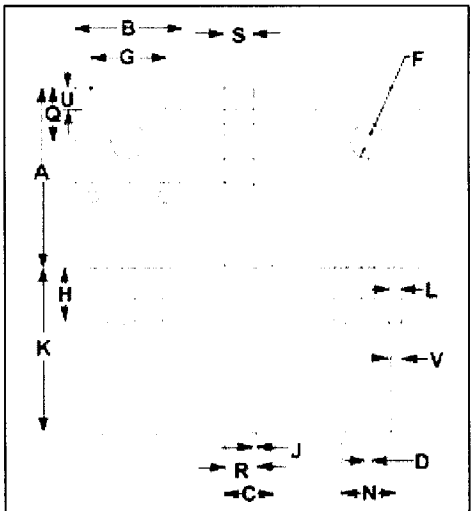


APPLICATIONS

- Designed for power amplifications and TV vertical deflection output applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-3	A
P_C	Collector Power Dissipation @ T_a=25℃	2	W
	Collector Power Dissipation @ T_C=25℃	30	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	16.85	17.15
B	9.54	10.10
C	4.35	4.65
D	0.75	0.90
F	3.20	3.40
G	6.90	7.20
H	5.15	5.45
J	0.45	0.75
K	13.35	13.65
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.55	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -5mA; I_B= 0	-150			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -50μ A; I_E= 0	-200			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -0.5mA; I_C= 0	-6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA			-1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -0.4A; V_{CE}= -10V			-1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -200V; I_E= 0			-50	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= -4V; I_C= 0			-50	μ A
h_{FE-1}	DC Current Gain	I_C= -150mA; V_{CE}= -10V	60		240	
h_{FE-2}	DC Current Gain	I_C= -0.4A; V_{CE}= -10V	50			
f_T	Current-Gain—Bandwidth Product	I_C=-0.5A; V_{CE}= -10V; f_{test}=10MHz		30		MHz

◆ **h_{FE-1} Classifications**

Q	P
60-140	100-240